

ABSTRACT OF THE DISCLOSURE

In a semiconductor device having a multilayer metallization structure using SiOF film as an interlayer insulating film, with respect to the interlayer insulating film, the fluorine concentration of SiOF films (11, 16) in a wiring gap portion in the same layer wiring is set to be higher than the fluorine concentration of SiOF films (12, 17) between the upper and lower layer wirings (8, 15; 15, 20).

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